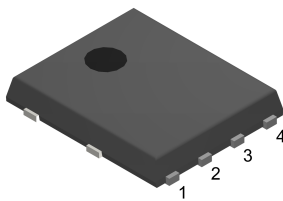
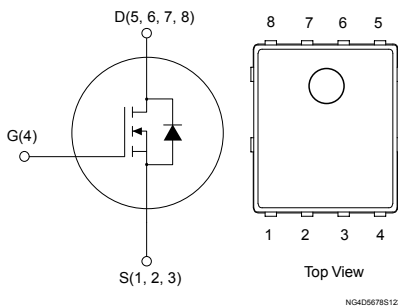


N-channel 30 V, 1.1 mΩ typ., 260 A, STripFET H6 Power MOSFET in a PowerFLAT 5x6 package



PowerFLAT 5x6



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STL260N3LLH6	30 V	1.3 mΩ	260 A

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the STripFET H6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R_{DS(on)} in all packages.



Product status link

[STL260N3LLH6](#)

Product summary

Order code	STL260N3LLH6
Marking	260N3LH6
Package	PowerFLAT 5x6
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	260	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	190	
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	1040	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	45	A
	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	32	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	180	A
$P_{TOT}^{(1)}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	166	W
$P_{TOT}^{(3)}$	Total power dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.8	W
$E_{AS}^{(4)}$	Single pulse avalanche energy	900	mJ
T_{stg}	Storage temperature range	-55 to 175	$^\circ\text{C}$
T_J	Operating junction temperature range		$^\circ\text{C}$

1. The value is rated according to R_{thj-c} .
2. Pulse width limited by safe operating area.
3. The value is rated according to $R_{thj-pcb}$.
4. Starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = 35\text{ A}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.9	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	

1. When mounted on an 1-inch² FR-4, 2 Oz copper board, $t < 10\text{ s}$.

2 Electrical characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	30			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 30\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 30\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}^{(1)}$			10	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1			V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 22.5\text{ A}$		1.1	1.3	m Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 22.5\text{ A}$		1.6	2.0	

1. Defined by design, not subject to production test.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	6375	-	pF
C_{oss}	Output capacitance		-	1230	-	
C_{rss}	Reverse transfer capacitance		-	675	-	
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 45\text{ A}$, $V_{GS} = 0\text{ to }4.5\text{ V}$ (see Figure 13. Test circuit for gate charge behavior)	-	61.5	-	nC
Q_{gs}	Gate-source charge		-	20	-	
Q_{gd}	Gate-drain charge		-	24	-	
R_g	Gate input resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	1.4	-	Ω

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}$, $I_D = 22.5\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	22.5	-	ns
t_r	Rise time		-	32	-	
$t_{d(off)}$	Turn-off delay time	(see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	107.5	-	
t_f	Fall time		-	54	-	

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		45	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		180	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 45\text{ A}$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 45\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 25\text{ V}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	37.2		ns
Q_{rr}	Reverse recovery charge		-	36		nC
I_{RRM}	Reverse recovery current		-	1.9		A

1. Pulse width is limited by safe operating area.
2. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

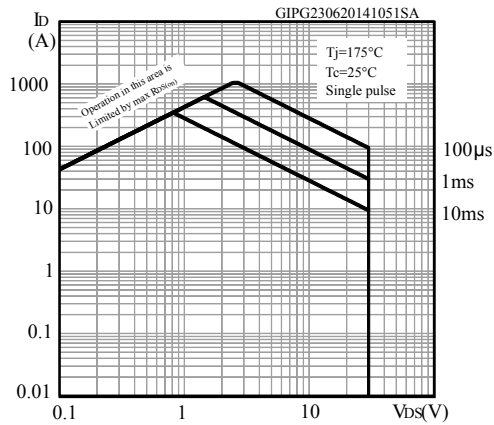
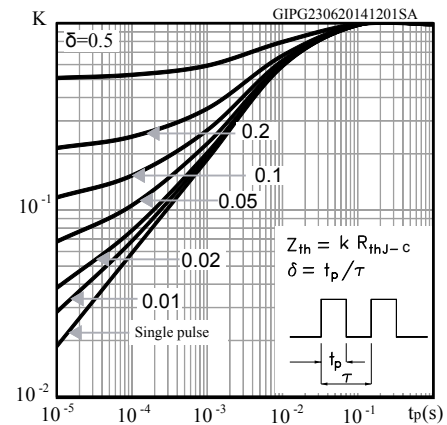
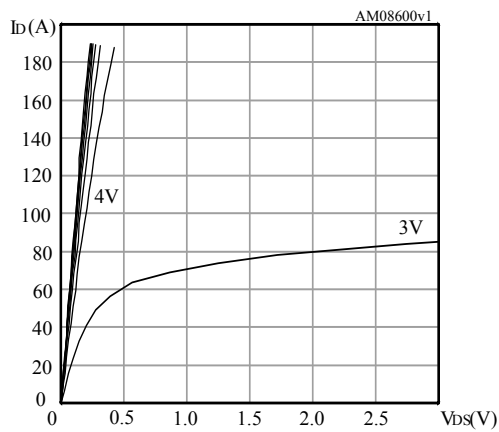
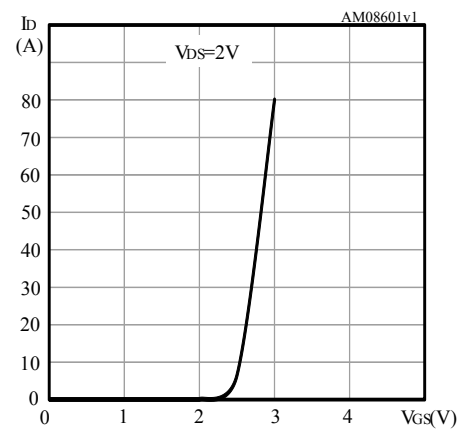
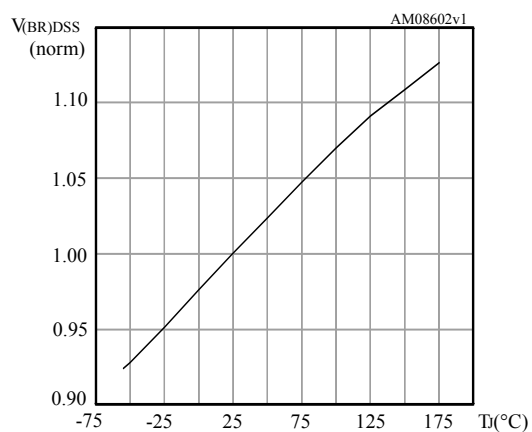
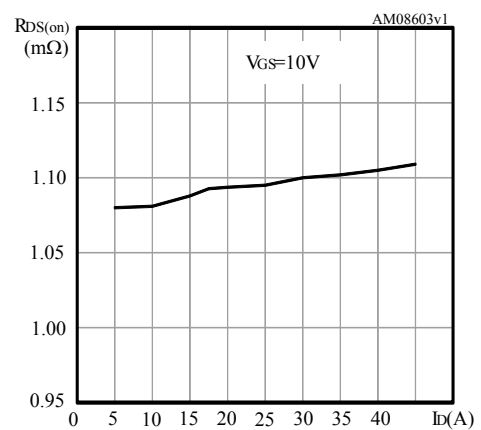
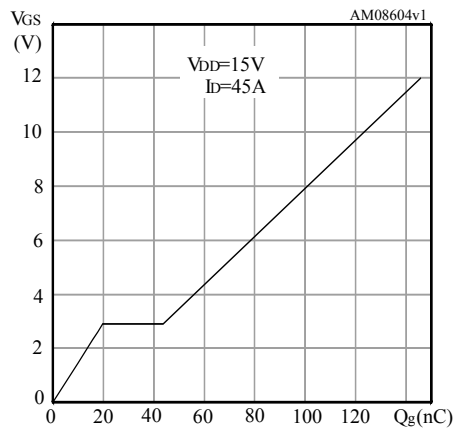
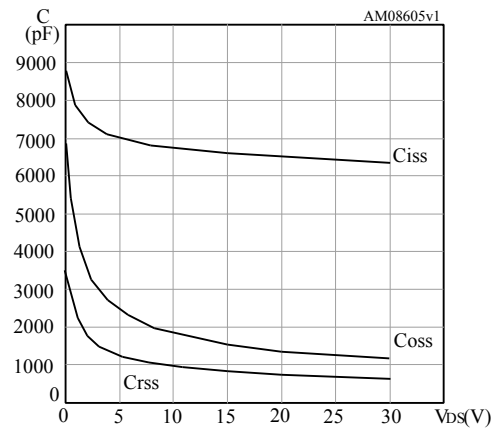
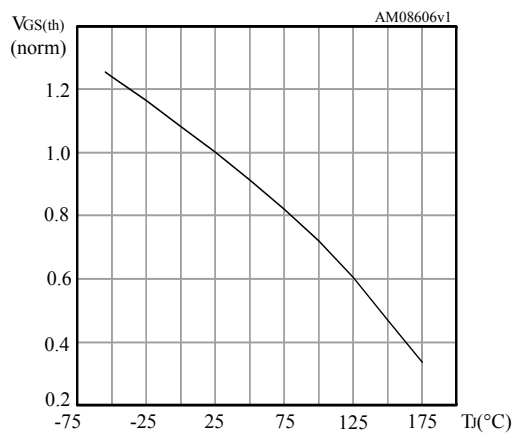
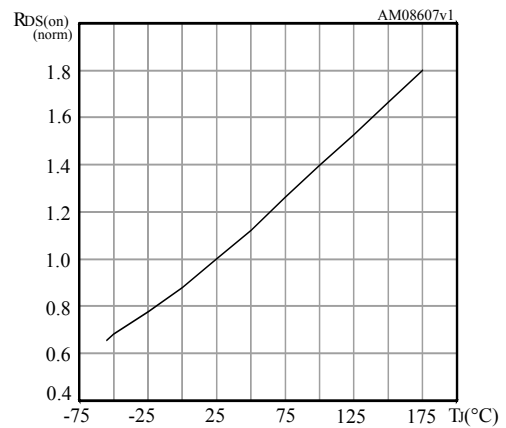
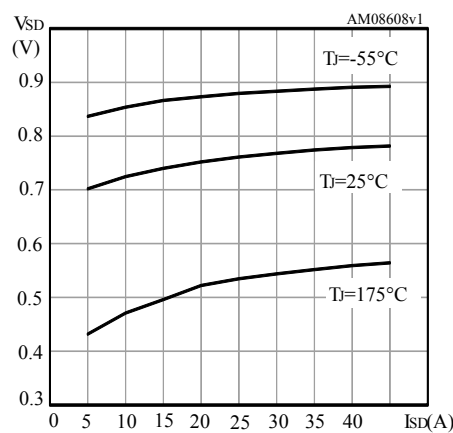
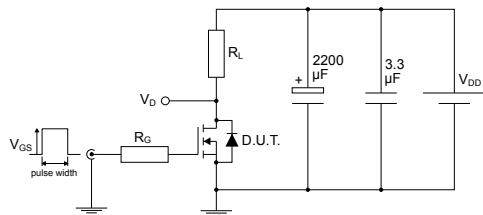
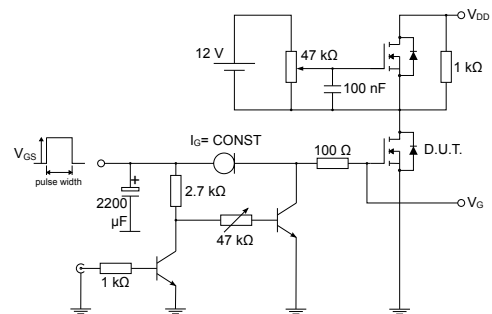
Figure 1. Safe operating area

Figure 2. Thermal impedance

Figure 3. Output characteristics

Figure 4. Transfer characteristics

Figure 5. Normalized $V_{(BR)DSS}$ vs temperature

Figure 6. Static drain-source on-resistance


Figure 7. Gate charge vs gate-source voltage

Figure 8. Capacitance variations

Figure 9. Normalized gate threshold voltage vs temperature

Figure 10. Normalized on-resistance vs temperature

Figure 11. Source-drain diode forward characteristics


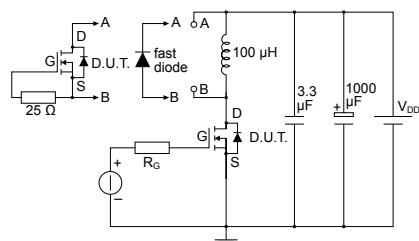
3 Test circuits

Figure 12. Test circuit for resistive load switching times


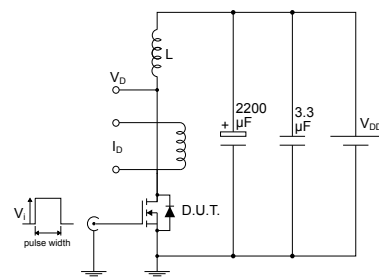
AM01468v1

Figure 13. Test circuit for gate charge behavior


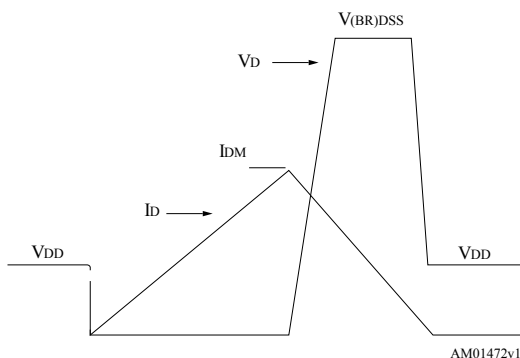
AM01469v1

Figure 14. Test circuit for inductive load switching and diode recovery times


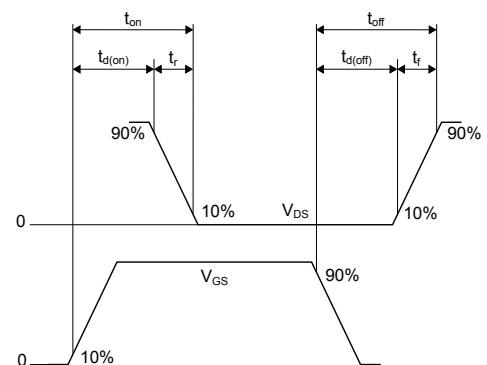
AM01470v1

Figure 15. Unclamped inductive load test circuit


AM01471v1

Figure 16. Unclamped inductive waveform


AM01472v1

Figure 17. Switching time waveform


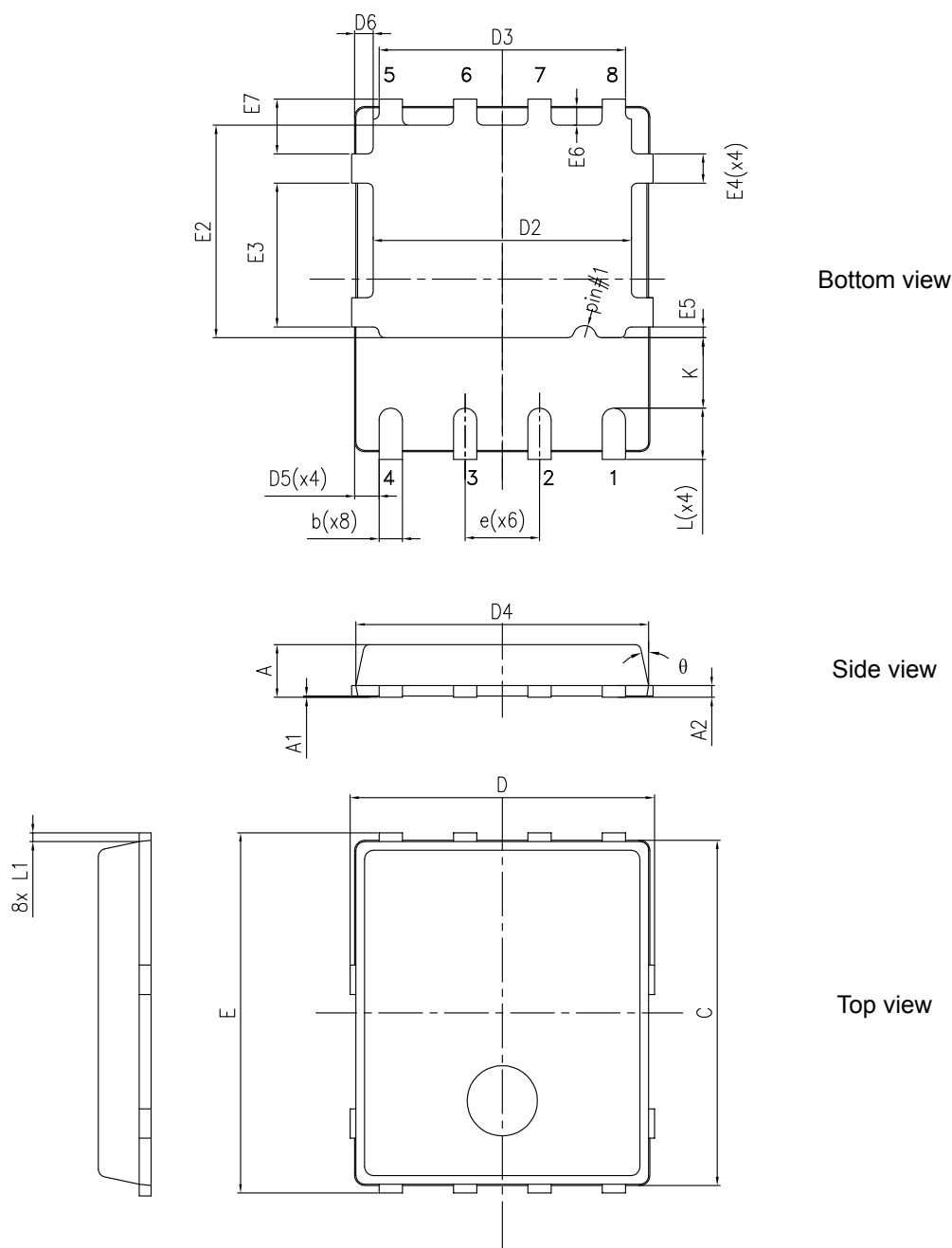
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 PowerFLAT 5x6 type C package information

Figure 18. PowerFLAT 5x6 type C package outline



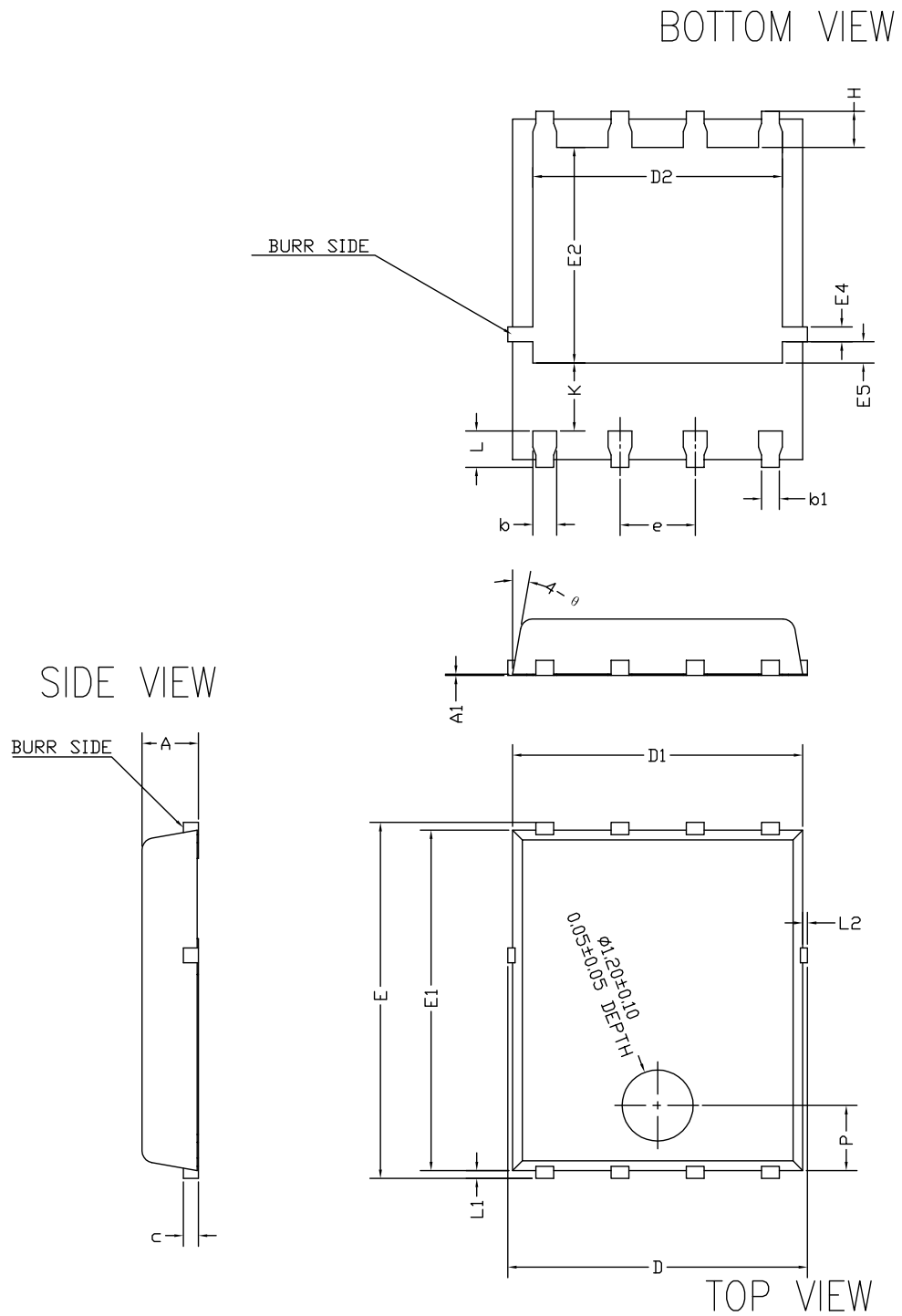
8231817_typeC_Rev20

Table 7. PowerFLAT 5x6 type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.20
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.20
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
e		1.27	
E	5.95	6.15	6.35
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.75	0.90	1.05
K	1.05		1.35
L	0.725		1.025
L1	0.05	0.15	0.25
θ	0°		12°

4.2 PowerFLAT 5x6 type C SUBCON package information

Figure 19. PowerFLAT 5x6 type C SUBCON package outline

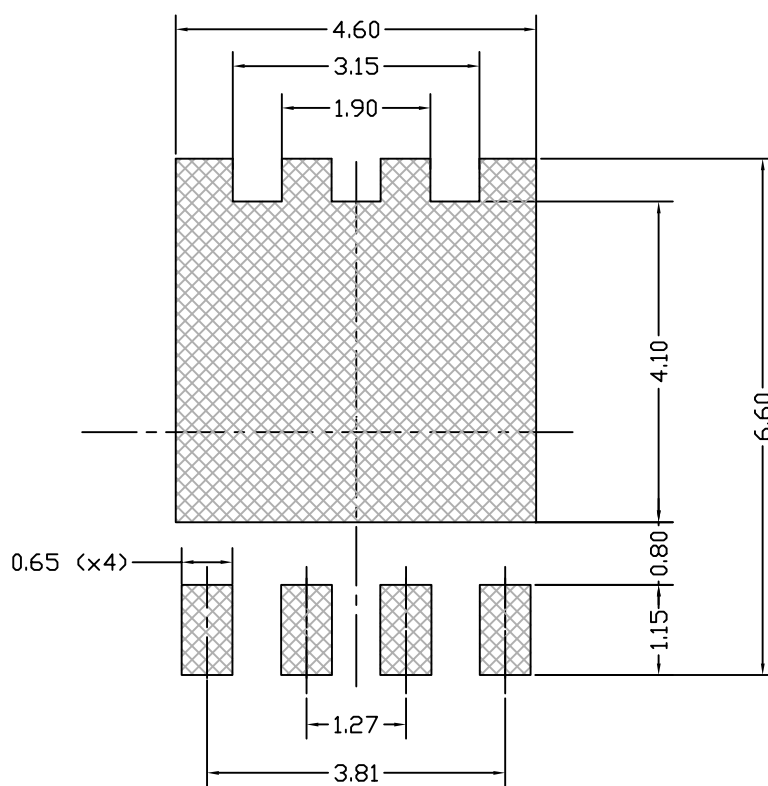


8472137_SUBCON_998G_REV4

Table 8. PowerFLAT 5x6 type C SUBCON package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.90	0.95	1.00
A1		0.02	
b	0.35	0.40	0.45
b1		0.30	
c	0.21	0.25	0.34
D			5.10
D1	4.80	4.90	5.00
D2	4.01	4.21	4.31
e	1.17	1.27	1.37
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.54	3.64	3.74
E4	0.15	0.25	0.35
E5	0.26	0.36	0.46
H	0.51	0.61	0.71
K	0.95		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
L2			0.10
P	1.00	1.10	1.20
θ	8°	10°	12°

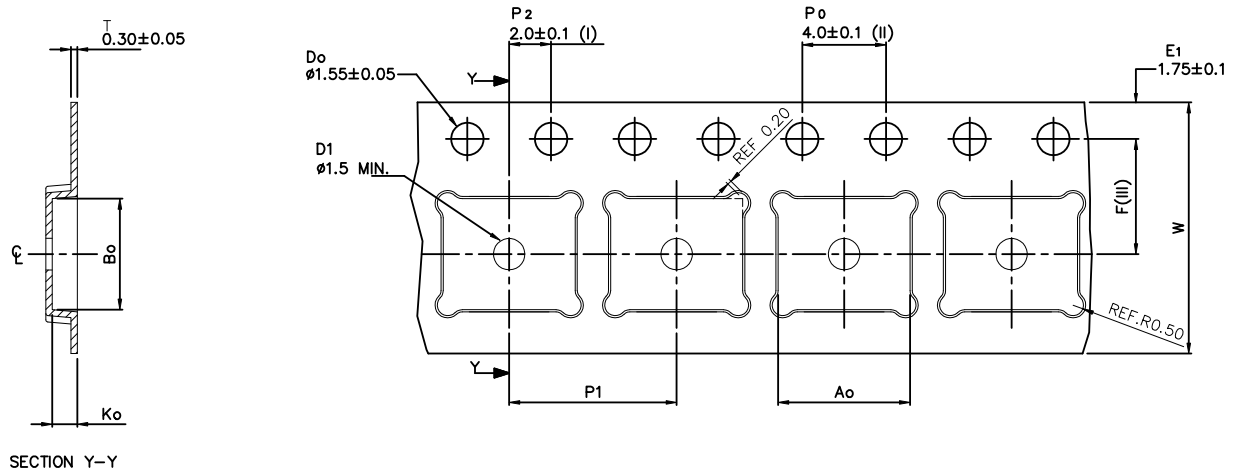
Figure 20. PowerFLAT 5x6 recommended footprint (dimensions are in mm)



8231817_FOOTPRINT_simp_Rev_20

4.3 PowerFLAT 5x6 packing information

Figure 21. PowerFLAT 5x6 tape (dimensions are in mm)



Ao	6.30 +/– 0.1
Bo	5.30 +/– 0.1
Ko	1.20 +/– 0.1
F	5.50 +/– 0.1
P1	8.00 +/– 0.1
W	12.00 +/– 0.3

(I) Measured from centreline of sprocket hole to centreline of pocket.

(II) Cumulative tolerance of 10 sprocket holes is ± 0.20 .

(III) Measured from centreline of sprocket hole to centreline of pocket

Base and bulk quantity 3000 pcs
All dimensions are in millimeters

8234350_Tape_rev_C

Figure 22. PowerFLAT 5x6 package orientation in carrier tape

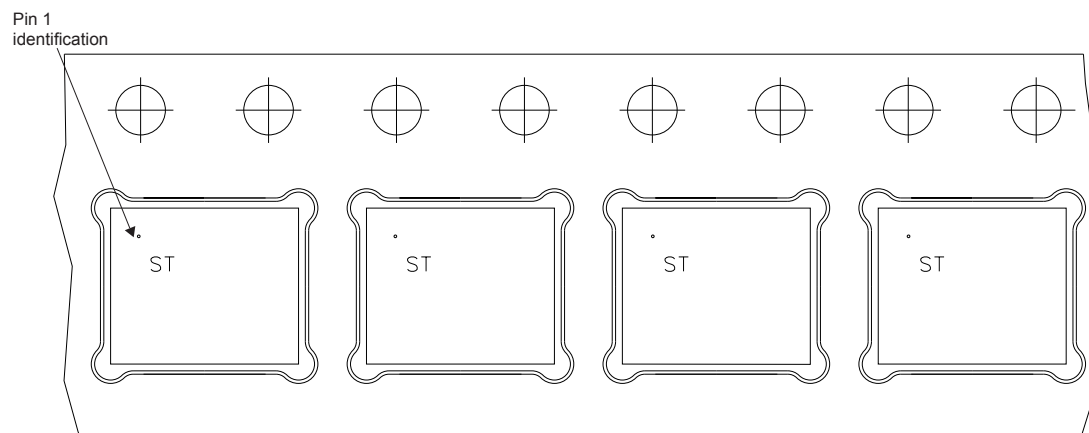
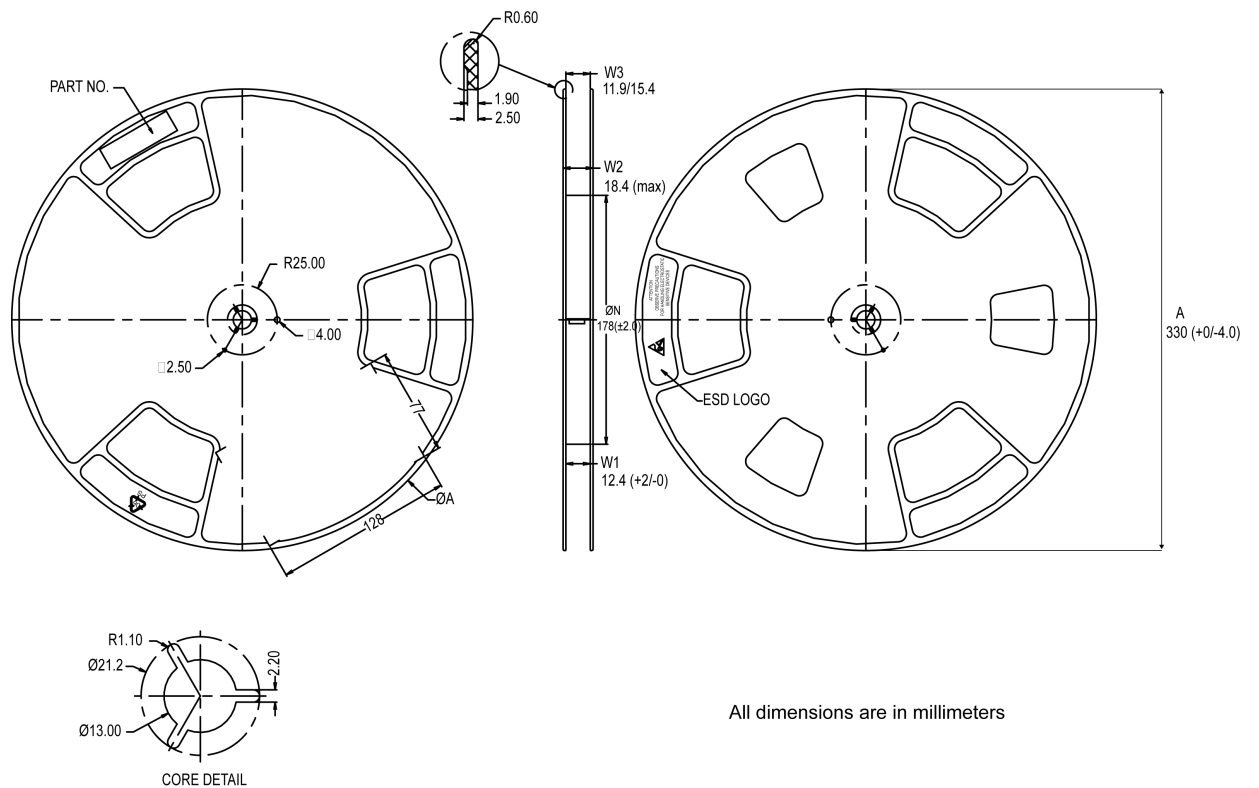


Figure 23. PowerFLAT 5x6 reel



8234350_Reel_rev_C

Revision history

Table 9. Document revision history

Date	Version	Changes
03-Aug-2014	1	First release.
03-Nov-2014	2	Updated value <i>Table 2: Electrical characteristics</i> Minor text changes
06-Feb-2019	3	Removed maturity status indication from cover page. The document status is production data. Updated marking information in Product summary table in cover page. Updated <i>Section 4 Package information</i> . Minor text changes.
14-Feb-2020	4	Updated Section 4 Package information . Minor text changes.

Contents

1	Electrical ratings	2
2	Electrical characteristics.....	3
2.1	Electrical characteristics (curves)	5
3	Test circuits	7
4	Package information.....	8
4.1	PowerFLAT 5x6 type C package information.....	8
4.2	PowerFLAT 5x6 type C SUBCON package information.....	9
4.3	PowerFLAT 5x6 packing information	12
	Revision history	15

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, please refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2020 STMicroelectronics – All rights reserved